

B1
Paul

48. (Amended) The method in claim 47, wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas and wherein said step of exposing said wafer in situ to an N₂/H₂ plasma comprises exposing said wafer in situ to said N₂/H₂ plasma prior to said step of exposing said wafer to silane gas.

Please add new claims 76-79 as follows:

Sub
PC1

--76. (New) A method of treating a wafer, comprising:
depositing a first conductive layer onto the wafer;
exposing the wafer in situ to a reducing environment; and
depositing a second conductive layer; and
exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof.

B2

77. (New) The method of claim 76 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

Sub
PC2

78. (New) The method of claim 76 wherein exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof comprises exposing the wafer to this selection prior to exposing the wafer in situ to a reducing environment.

79. (New) The method of claim 76 wherein exposing the wafer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof comprises exposing the wafer to this selection prior to depositing the second conductive layer.--